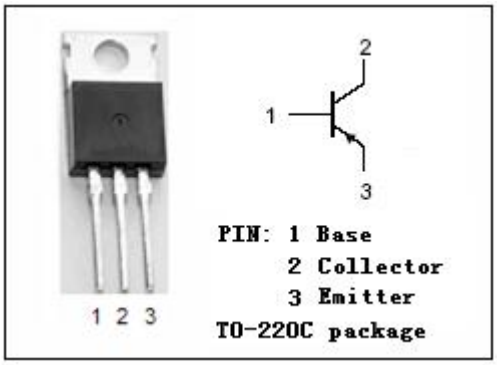
isc Silicon PNP Power Transistor 2SB547

DESCRIPTION

- Collector-Emitter Breakdown Voltage-
  : $V_{(BR)CEO}$= -150V (Min)
- Collector Power Dissipation-
  : P_C= 30W(Max)@ T_C= 25℃
- Complement to Type 2SD402
- Minimum Lot-to-Lot variations for robust device performance and reliable operation



APPLICATIONS

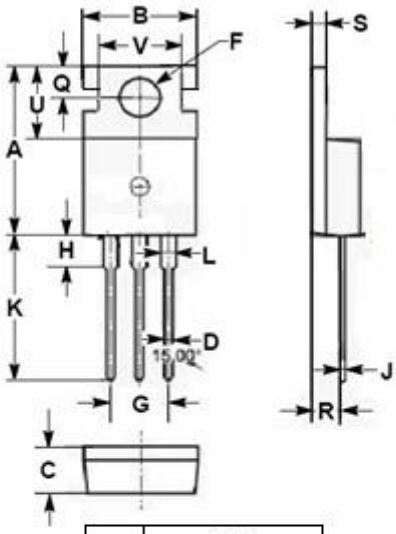
- Designed for use in line-operated color TV vertical deflection of complementary symmetry circuit applications.

ABSOLUTE MAXIMUM RATINGS(T_a=25℃)

SYMBOL	PARAMETER	VALUE	UNIT
V_{CBO}	Collector-Base Voltage	-200	V
V_{CEO}	Collector-Emitter Voltage	-150	V
V_{EBO}	Emitter-Base Voltage	-5.0	V
I_C	Collector Current-Continuous	-2	A
I_{CM}	Collector Current-Peak	-3	A
I_{BM}	Base Current-Peak	-1.5	A
P_C	Total Power Dissipation @ T_C=25℃	30	W
T_J	Junction Temperature	150	℃
T_{stg}	Storage Temperature Range	-55~150	℃

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	MAX	UNIT
$R_{th\ j\text{-}a}$	Thermal Resistance,Junction to Ambient	78	℃/W
$R_{th\ j\text{-}c}$	Thermal Resistance,Junction to Case	4.16	℃/W



DIM	mm MIN	mm MAX
A	15.50	15.90
B	9.80	10.20
C	4.20	4.50
D	0.70	0.90
F	3.40	3.70
G	4.98	5.18
H	2.68	2.90
J	0.44	0.60
K	12.80	13.40
L	1.20	1.45
Q	2.70	2.90
R	2.30	2.70
S	1.29	1.35
U	6.45	6.65
V	8.66	8.86

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ELECTRICAL CHARACTERISTICS

Tj=25℃ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{(BR)CEO}$	Collector-Emitter Breakdown Voltage	I_C= -10mA ; I_B= 0	-150			V
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	I_C= -0.5A; I_B= -50mA			-2.0	V
I_{CBO}	Collector Cutoff Current	V_{CB}= -150V ; I_E= 0			-50	μA
I_{EBO}	Emitter Cutoff Current	V_{EB}= -4V; I_C= 0			-50	μA
h_{FE}	DC Current Gain	I_C= -0.4A ; V_{CE}= -10V	40			
f_T	Current-Gain—Bandwidth Product	I_C= -0.4A ; V_{CE}= -10V		7		MHz
C_{OB}	Output Capacitance	I_E= 0; V_{CB}= -10V;f_{test}= 1MHz		75		pF